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- 오류정정 -

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논문제목	“나노 소재 기반의 전기장 투과 전극에 관한 연구동향”
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	22. G. Gao, T. Workman, L. Mirkarimi, G. Fountain, J. Theil, G. Guevara, C. Uzoh, B. Lee, P. Liu
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	22. G. Gao, T. Workman, L. Mirkarimi, G. Fountain, J. Theil, G. Guevara, C. Uzoh, B. Lee, P. Liu, and P. Mrozek, “Chip to Wafer Hybrid Bonding with Cu Interconnect: High Volume Manufacturing Process Compatibility Study”, International Wafer-Level Packaging Conference (IWLPC), San Jose (2019).
요청부분	(pp.23) 참고문헌 23번-39번 전체 번호 오류
	23. , and P. Mrozek, “Chip to Wafer Hybrid Bonding with Cu Interconnect: High Volume Manufacturing Process Compatibility Study”, International Wafer-Level Packaging Conference (IWLPC), San Jose (2019). 24. R. He, M. Fujino, A. Yamauchi, and T. Suga, “Combined Surface Activated Bonding Technique for Hydrophilic SiO2-SiO2 and Cu-Cu Bonding”, ECS Transactions, 75(9), 117 (2016). 25. T. Wlanis, R. Hammer, W. Ecker, S. Lhostis, C. Sart, S. Gallois- Garreignot, B. Rebhan, and G. A. Maier, “Cu-SiO2 hybrid bonding simulation including surface roughness and viscoplastic material modeling: A critical comparison of 2D and 3D modeling approach”, Microelectron. Reliab., 86, 1 (2018). 26. K. N. Chen, Z. Xu, and J. Q. Lu, “Demonstration and Electrical Performance Investigation of Wafer-Level Cu Oxide Hybrid Bonding Schemes”, IEEE Electron Device Lett., 32(8), 1119 (2011). 27. S. Kim, P. Kang, T. Kim, K. Lee, J. Jang, K. Moon, H. Na, S. Hyun, and K. Hwang, “Cu Microstructure of High Density Cu Hybrid Bonding Interconnection”, Proc. 69th Electronic Components and Technology Conference (ECTC), Las Vegas, 636, IEEE (2019). 28. J. Morrison, R. Fontaine, D. James, and D. Yang, “Samsung Galaxy S7 Edge Teardown”, April (2016) from http://www.chipworks.com/about-chipworks/overview/blog/samsung-galaxy-s7-edge-teardown 29. P. Morrow, M. J. Kobrinsky, S. Ramanathan, C. M. Park, M. Harmes, V. Ramachandrarao, H. Park, G. Kloster, S. List, and S. Kim, “Wafer-Level 3D Interconnects Via Cu Bonding”, Proc. Advanced Metallization Conference, San Diego (2004).

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31. Z. J. Hu, X. P. Qu, H. Lin, R. D. Huang, X. C. Ge, M. Li, S. M. Chen, and Y. H. Zhao, “Cu CMP process development and characterization of Cu dishing with 1.8 μm Cu pad and 3.6 μm pitch in Cu/SiO2 hybrid bonding”, Jap. J. Appl. Phys., 58(SH), SHHC01 (2019).
32. L. Di Cioccio, P. Gueguen, R. Taibi, D. Landru, G. Gaudin, C. Chappaz, F. Rieutord, F. de Crecy, I. Radu, L. L. Chapelon, and L. Clavelier, “An Overview of Patterned Metal/Dielectric Surface Bonding: Mechanism, Alignment and Characterization”, J. Electrochem. Soc., 158(6), 81 (2011).
33. C. M. Liu, H. W. Lin, Y. C. Chu, C. Chen, D. R. Lyu, K. N. Chen, and K. N. Tu, “Low-temperature direct copper-to-copper bonding enabled by creep on highly (1 1 1)-oriented Cu surfaces”, Scr. Mater., 78–79, 65 (2014).
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35. J. Y. Juang, C. L. Lu, K. J. Chen, C. C. A. Chen, P. N. Hsu, C. Chen, and K. N. Tu, “Copper-to-copper direct bonding on highly (111)-oriented nanotwinned copper in no-vacuum ambient”, Sci. Rep., 8, 13910 (2018).
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38. R. He, M. Fujino, A. Yamauchi, Y. Wang, and T. Suga, “Combined Surface Activated Bonding Technique for Low-Temperature Cu/Dielectric Hybrid Bonding”, ECS J. Solid State Sci. Technol., 5(7), 419 (2016).
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<tr><td rowspan="2">정 정</td><td>(pp.31) 참고문헌 23번-38번까지로 표기 수정</td></tr>
<tr><td>23. R. He, M. Fujino, A. Yamauchi, and T. Suga, “Combined Surface Activated Bonding Technique for Hydrophilic SiO2-SiO2 and Cu-Cu Bonding”, ECS Transactions, 75(9), 117 (2016).
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학회지 및 페이지	J. Microelectron. Packag. Soc., 27(1), 25 (2020)
논문제목	“광화학증착법에 의한 직접패턴 비정질 TiOx 박막의 제조 및 저항변화 특성”
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요청부분	18. B. J. Choi, D. S. Jeong, and S. K. Kim, “Resistive switching mechanism of TiO2 thin films grown by atomic-layer deposition”, J. Appl. Phys., 98(3), 033715 (2005). 19. D.-H. Kwon, K. M. Kim, J. H. Jang, J. M. Jeon, M. H. Lee, G. H. Kim, X.-S. Li, G.-S. Park, B. Lee, S. Han, M. Kim 20. , and C. S. Hwang, “Atomic structure of conducting nanofilaments in TiO2 resistive switching memory”, Nat. Nanotechnol., 5(2), 148 (2010). 21. Z.-X. Lu, X. Song, L.-N. Zhao, Z.-W. Li, Y.-B. Lin, M. Zeng, Z. Zhang, X.-B. Lu, S.-J. Wu, X.-S. Gao, Z.-B. Yan, and J.-M. Liu, “Temperature dependences of ferroelectricity and resistive switching behavior of epitaxial BiFeO3 thin films”, Chin. Phys. B, 24(10), 107705 (2015).
정 정	(pp.29) 참고문헌 9번-18번 전체 번호 수정. 중복 번호 9번, 18번 삭제. 번호 오류 19, 20번 하나로 합침.
	9. B. J. Choi, D. S. Jeong, and S. K. Kim, “Resistive switching mechanism of TiO2 thin films grown by atomic-layer deposition”, J. Appl. Phys., 98(3), 033715 (2005). 10. H. S. Lee, S. G. Choi, H.-H. Park, and M. J. Rozenberg, “A new route to the Mott-Hubbard metal-insulator transition: Strong correlations effects in Pr0.7Ca0.3MnO3”, Sci. Rep., 3, 1704 (2013). 11. J.-S. Hwang, W.-S. Kim, H.-H. Park, and T.-S. Kim “Sol-gel Mechanism of Self-patternable PZT Film Starting from Alkoxides Precursors”, J. Korean Ceram. Soc., 40(4), 285 (2003). 12. H.-H. Park, S. Yoon, H.-H. Park, and R. H. Hill, “Electrical properties of PZT thin films by photochemical deposition”, Thin Solid Films, 447-448, 669 (2004). 13. C.-S. Hong, H.-H. Park, S.-J. Wang, J. H. Moon, H.-H. Park, and R. H. Hill, “Formation of photoresist-free patterned ZnO film containing nano-sized Ag by photochemical solution deposition”, Appl. Surf. Sci., 252(21), 7739 (2006). 14. W. J. Potts, and R. A. Nyquist, “Factors affecting the out-of plane hydrogen deformation frequencies in olefins and their derivatives”, Spectrochim. Acta A, 15, 679 (1959). 15. H.-H. Park, H.-H. Park, and R. H. Hill, “Direct-patterning of SnO2 thin film by photochemical metal-organic deposition”, Sens. Actuators, A, Phys., 132(2), 429 (2006). 16. M.-J. Lee, C. B. Lee, D. Lee, S. R. Lee, M. Chang, J. H. Hur, Y.-B. Kim, C.-J. Kim, D. H. Seo, S. Seo, U.-I. Chung, I.-K. Yoo, and K. Kim, “A fast, high-endurance and scalable nonvolatile memory device made from asymmetric Ta2O5-x/TaO2-x bilayer structures”, Nat. Mater., 10(8), 625 (2011). 17. D.-H. Kwon, K. M. Kim, J. H. Jang, J. M. Jeon, M. H. Lee, G. H. Kim, X.-S. Li, G.-S. Park, B. Lee, S. Han, M. Kim, and C. S. Hwang, “Atomic structure of conducting nanofilaments in TiO2 resistive switching memory”, Nat. Nanotechnol., 5(2), 148 (2010). 18. Z.-X. Lu, X. Song, L.-N. Zhao, Z.-W. Li, Y.-B. Lin, M. Zeng, Z. Zhang, X.-B. Lu, S.-J. Wu, X.-S. Gao, Z.-B. Yan, and J.-M. Liu, “Temperature dependences of ferroelectricity and resistive switching behavior of epitaxial BiFeO3 thin films”, Chin. Phys. B, 24(10), 107705 (2015).

학회지 및 페이지	J. Microelectron. Packag. Soc., 27(1), 55 (2020)
논문제목	“Solid Epoxy를 이용한 패키지 및 솔더 크랙 신뢰성 확보를 위한 실험 및 수치해석 연구”
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실험 및 수치해석 연구”</td></tr>
<tr><td rowspan="2">요청부분</td><td>(pp.72) 참고문헌 표기 오류</td></tr>
<tr><td>10. S. H. Cho D. H. Kim, Y. G. Oh, J. T. Lee, and S. S. Cha, “A Study on the Parameters of Design for Warpage reduction of Passive components Embedded Substrate for PoP”, J. Microelectron. Packag. Soc., 22(1), 75 (2015).</td></tr>
<tr><td rowspan="2">정 정</td><td>(pp.72) 참고문헌 표기 쉼표 삽입</td></tr>
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